

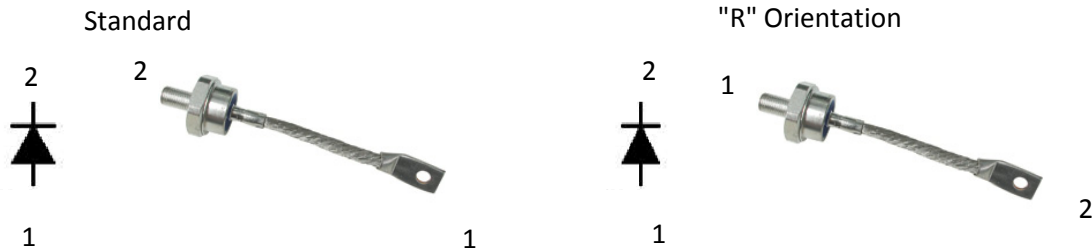
Silicon Standard Recovery Diode

$V_{RRM} = 200\text{ V} - 1400\text{ V}$
 $I_F = 150\text{ A}$

Features

- High Surge Capability
- Types up to 1400 V V_{RRM}

DO-8 Package



Maximum ratings, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	1N4594(R)	1N4595(R)	1N4596(R)	Unit
Repetitive peak reverse voltage	V_{RRM}		1000	1200	1400	V
DC blocking voltage	V_{DC}		1000	1200	1400	V
Continuous forward current	I_F	$T_C \leq 110\text{ }^{\circ}\text{C}$	150	150	150	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 8.3\text{ ms}$	3000	3000	3000	A
I_2t for fusing	I_2t	60 Hz Half wave	37200	37200	37200	A^2sec
Operating temperature	T_j		-60 to 200	-60 to 200	-60 to 200	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-60 to 200	-60 to 200	-60 to 200	$^{\circ}\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N4594(R)	1N4595(R)	1N4596(R)	Unit
Diode forward voltage	V_F	$I_F = 150\text{ A}$, $T_j = 110\text{ }^{\circ}\text{C}$	1.5	1.5	1.5	V
Reverse current	I_R	$V_R = V_{RRM}$, $T_j = 110\text{ }^{\circ}\text{C}$	4.5	4	3.5	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.35	0.35	0.35	$^{\circ}\text{C/W}$
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Electrical Characteristics

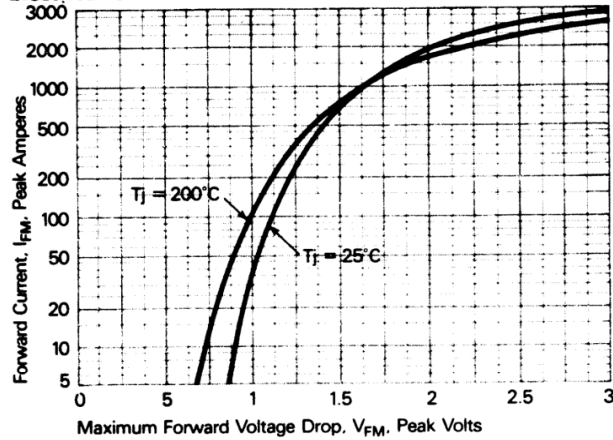


Figure 1. Forward current vs. Forward voltage.

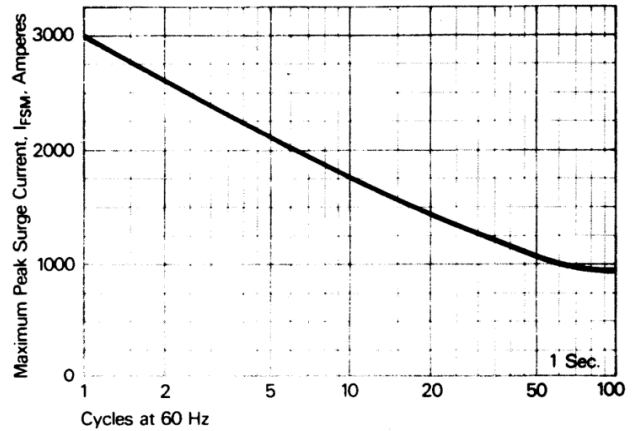


Figure 2. Maximum allowable surge current at rated load conditions.

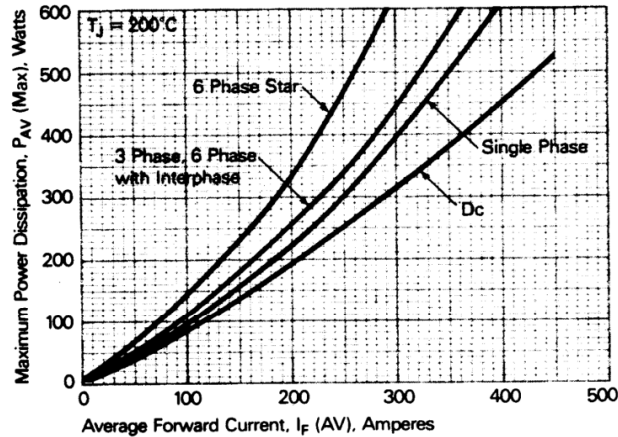


Figure 3. Power dissipation vs. Average forward current.

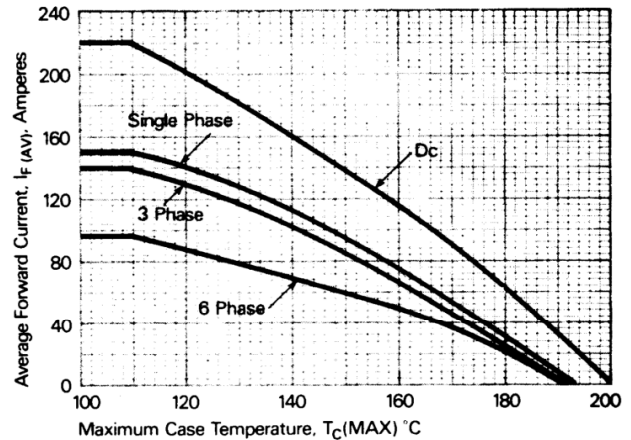


Figure 4. Forward current vs. Case temperature.